

# **TSM9428**

## 20V N-Channel MOSFET



SOP-8

#### Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
20	30 @ V <sub>GS</sub> = 4.5V	6.0	
	40 @ V <sub>GS</sub> = 2.5V	5.2	

### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

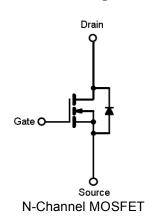
### **Application**

- Load Switch
- PA Switch

### **Ordering Information**

Part No.	Package	Packing
TSM9428CS RL	SOP-8	2.5Kpcs / 13" Reel

### **Block Diagram**



### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	eter Sym			Unit	
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V.		I <sub>D</sub>	6	Α	
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub> 20		Α	
Continuous Source Current (Diode Cor	nduction) <sup>a,b</sup>	I <sub>S</sub>	1.7	Α	
Maximum Dowar Dissination	Ta = 25°C	P <sub>D</sub>	2.5	W	
Maximum Power Dissipation	Ta = 70°C		1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ <sub>JF</sub>	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

1/6

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.

Version: A07



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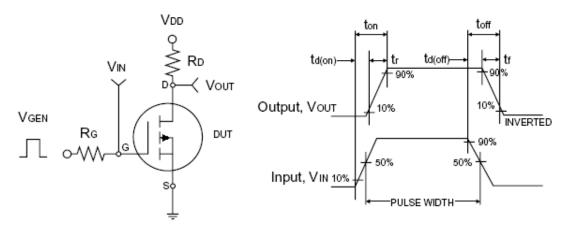


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	•	1				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V <sub>GS(TH)</sub>	0.45	0.65	0.85	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>	-		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
On-State Drain Current	V <sub>DS</sub> ≥5V, V <sub>GS</sub> = 4.5V	I <sub>D(ON)</sub>	20			Α
Drain Source On State Desigtance	$V_{GS} = 4.5V, I_D = 6.0A$		1	23	30	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	$R_{DS(ON)}$		28	40	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.0A$	g <sub>fs</sub>		24		S
Diode Forward Voltage	I <sub>S</sub> = 1.0A, V <sub>GS</sub> = 0V	$V_{SD}$			1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ - 10\/   - 6A	$Q_g$		11	14	
Gate-Source Charge	$V_{GS} = 2.5V, I_D = 5.2A$ $V_{DS} = 10V, I_D = 6.0A$ $I_S = 1.0A, V_{GS} = 0V$ $V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$ $V_{DS} = 10V, V_{GS} = 0V,$	$Q_gs$		1.5		nC
Gate-Drain Charge	V <sub>GS</sub> = 4.5 V	$Q_gd$	-	2.1		
Input Capacitance	\\ -40\\\\\ -0\\	C <sub>iss</sub>		900		
Output Capacitance	$v_{DS} = 10V, v_{GS} = 0V,$ - f = 1.0MHz	$C_{oss}$		140		pF
Reverse Transfer Capacitance	7 I = 1.0IVID2	C <sub>rss</sub>		100		
Switching <sup>c</sup>						
Turn-On Delay Time	V 40V D 400	t <sub>d(on)</sub>		0.53	0.8	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t <sub>r</sub>		1.4	2.2	20
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$	t <sub>d(off)</sub>		13.5	20	nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t <sub>f</sub>		5.9	9	

#### Notes:

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms



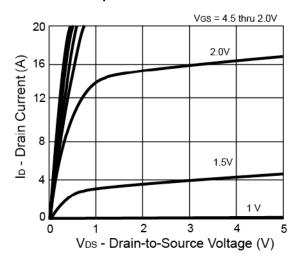




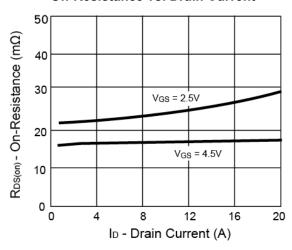


### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

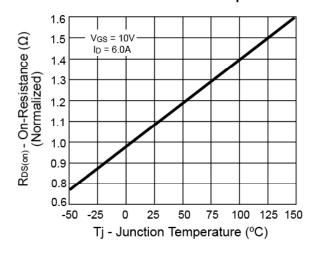
#### **Output Characteristics**



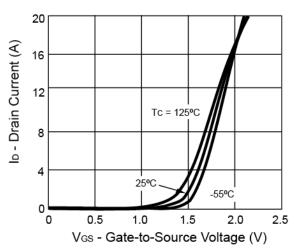
#### **On-Resistance vs. Drain Current**



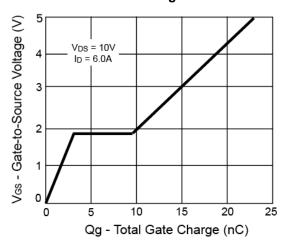
#### On-Resistance vs. Junction Temperature



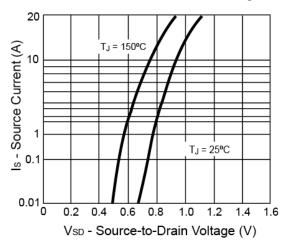
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage





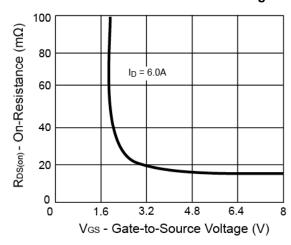






#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage



# 0.4 0.2 -0.0 -0.2 -0.4 -0.6

25

50

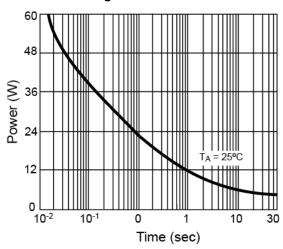
Tj - Junction Temperature (°C)

75

100 125 150

**Threshold Voltage** 

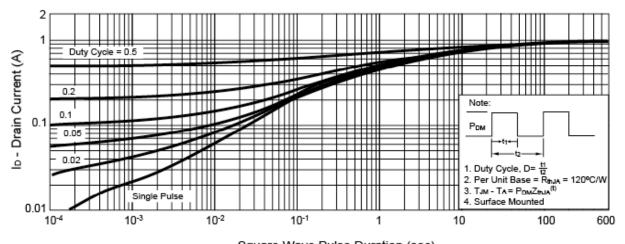
#### Single Pulse Power



### Normalized Thermal Transient Impedance, Junction-to-Ambient

Vgs(th) - Variance (V)

-50 -25



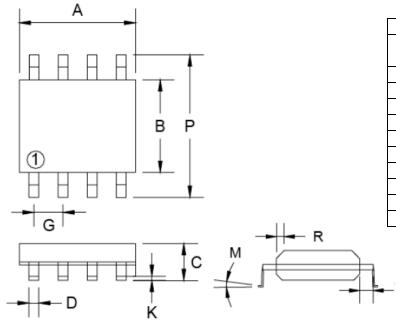
Square Wave Pulse Duration (sec)





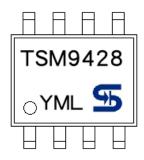


# **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
D	0.25	0.50	0.010	0.010	

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

**L** = Lot Code



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